

# Silicon-Based Technology Corp.

Small-Signal Schottky Barrier Diodes

SBT40Q Series

SBT40Q series are Schottky Barrier Diodes fabricated by a series of proprietary Schottky barrier patents and technologies (SBT<sup>®</sup>) developed by Silicon-Based Technology Corporation, which exhibit high-performance characteristics for modern switching, conversion and protection applications with high speed and low power consumptions. The package types as described in this data sheet are set forth in routine production; other packages are available upon special orders.

## ■ Features and Advantages:

- Low forward voltage drop ( $V_F$ )
- Low reverse leakage current ( $I_R$ )
- Very small conduction power loss
- Very small switching power loss
- Very high switching speed
- Very high reliability

## ■ Electrical Characteristics : (@ $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage (Note 2)	$V_{(BR)R}$	30	-	-	V	$I_R=100\mu\text{A}$
Forward Voltage (Note 2)	$V_F$	-	-	250 300 400 500 800	mV	$I_F=0.1\text{mA}$ , $t_p<300\mu\text{s}$ $I_F=1.0\text{mA}$ , $t_p<300\mu\text{s}$ $I_F=10\text{mA}$ , $t_p<300\mu\text{s}$ $I_F=30\text{mA}$ , $t_p<300\mu\text{s}$ $I_F=100\text{mA}$ , $t_p<300\mu\text{s}$
Reverse Current (Note 2)	$I_R$	-	-	2	$\mu\text{A}$	$V_R=25\text{V}$
Total Capacitance	$C_T$	-	10.0 6.5	-	pF	$V_R=0$ , $f=1.0\text{MHz}$ (Note 3) $V_R=0$ , $f=1.0\text{MHz}$ (Note 4)
Reverse Recovery Time	$t_{rr}$	-	-	5.0	ns	$I_F=I_R=10\text{mA}$ , $I_{rr}=0.1 \times I_R$ , $R_L=100\Omega$



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**■ Maximum Ratings : (@T<sub>A</sub>=25°C unless otherwise specified)**

<b>Characteristic</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>		
Working Peak Reverse Voltage	V <sub>RWM</sub>	30	V
DC Blocking Voltage	V <sub>R</sub>		
Forward Continuous Current (Note 1)	I <sub>FM</sub>	200	mA
Non-Repetitive Peak Forward Current @t<1.0s	I <sub>FSM</sub>	600	mA
Power Dissipation (Note 1)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R <sub>θJA</sub>	625	°C/W
Operating Temperature Range	T <sub>j</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +125	°C

Notes: 1. Device mounted on FR-4 PCB, 1 inch\*0.85 inch\*0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.sbt.com.tw>.

2. Short duration test pulse is used to minimize self-heating effect.

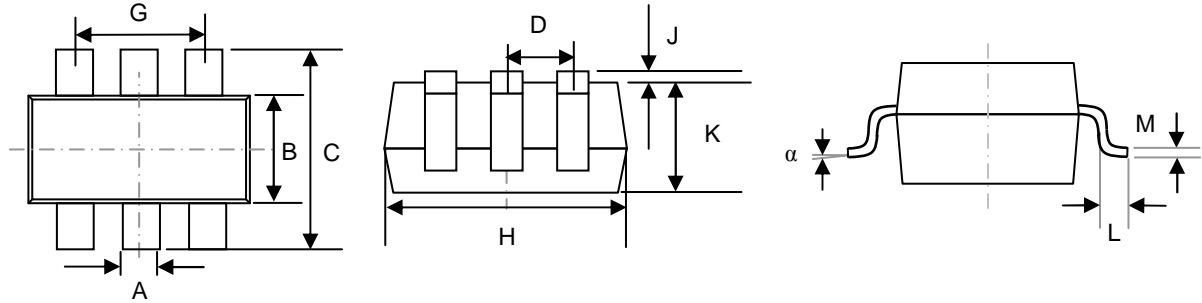
3. At V<sub>R</sub>=0V, DL(X) to V<sub>CC</sub> or GND.

4. At V<sub>R</sub>=0V, between Data Lines (e.g., DL1 and DL4).

**■ Package Data :**

- Case: Molded Plastic Material (UL Flammability Classification 94V-0)
- Terminals: Solderable Plated Terminals (MIL-STD-202, Method 208)
- Lead Free Plating (Matte Tin Finish)
- Polarity: See device configurations below
- Approx. Weight: 0.006 grams
- Package outline and dimensions (see below)

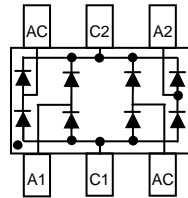
### SOT-363


**DIMENSIONS (MM)**

	A	B	C	D	F	H	J	K	L	M	$\alpha$
Min.	0.10	1.15	2.00	0.65	0.30	1.80	-	0.90	0.25	0.10	0°
Max.	0.30	1.35	2.20	Nominal	0.40	2.20	0.10	1.00	0.40	0.25	8°

#### ■ Device Configurations :

### TOP VIEW



#### ■ Ordering Information (Note 5)

Part Number	Marking Code	Packaging Type	Shipping
			7" Tape & Real
SBT40Q	SBT40Q	SOT-363	3K

Notes: 5. Website at <http://www.sbt.com.tw>

6. Bulk package in a box form is also available upon request.

7. Day code marking is YM, in which Y represents year (For example: 2005 is marked by 5);

M represents month in a year (For example: March is marked by C; November is marked by K).